Medium power Transistor(-32V, -2A) 2SB1188/2SB1182/2SB1240/2SB891F/ 2SB822/2SB1277/2SB911M

Features

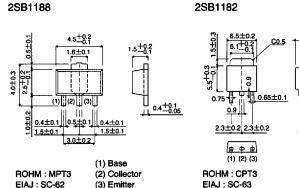
1) Low VCE(sat). $V_{CE(sat)} = -0.5V (Typ.)$ $(I_C/I_B = -2A/-0.2A)$

Complements the 2SD1766/ 2SD1758/2SD1862/2SD1189F/ 2SD1055/2SD19192/SD1227M.

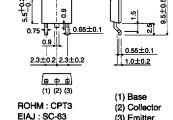
Structure Epitaxial planar type

PNP silicon transistor

External dimensions (Units: mm)



2SB891F

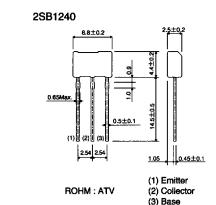


2SB822

(3) Emitter

0.5±0.1

Abbreviated symbol: BC *



ROHM: TO-126FP

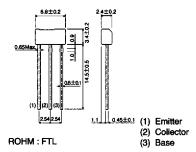
2.3±0.5 0.7±0.1 1.78±0.5 (n 23)

(1) Emitter (2) Collector (3) Base

 6.8 ± 0.2 254 254 (1) (2) (3)

(1) Emitter ROHM: FTR (2) Collector (3) Base

2SB911M



(1) Emitter

ROHM: ATR EIAJ: SC-71

(2) Collector (3) Base

*Denotes hre

2SB1277

7828999 0016861 330

(96-131-B24)

■Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit	
Collector-base voltage		Vсво	-40	V	
Collector-emitte	r voltage	VCEO	-32	V	
Emitter-base vo	Itage	VEBO	-5	V	
Callantan		1-	-2	A (DC)	
Collector curren	T 	lc	-3	A (Pulse) *1	
	2SB1188	Pc	0.5	144	
			2	- W *2	
.	2SB1182		10	W(Tc=25℃)	
Collector power dissipation	2SB1240,2SB911M		Pc 1	*3	
dissipation	2SB891F		1.2	- w -	
	2386915		5	W(Tc=25℃)	
	2SB822,2SB1277		0.75	W	
Junction temperature		Tj	150	C	
Storage tempera	ature	Tstg	−55 ~150	င	

^{*1} Single pulse Pw=100ms

●Electrical characteristics (Ta = 25°C)

Pa	rameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Collector-base breakdown voltage		ВУсво	-40	_	_	٧	lc=-50 μ A	
Collector-emitte	er breakdown voltage	BVCEO	-32			٧	Ic=-1mA	
Emitter-base br	eakdown voltage	ВУєво	-5	_	_	٧	I _E =-50 μ A	
Collector cutoff	current	Ісво		_	-1	μА	V _{CB} =-20V	
Emitter cutoff current		IEBO		_	-1	μΑ	V _{EB} =-4V	
Collector-emitte	er saturation voltage	VCE(sat)	_	-0.5	-0.8	٧	Ic/I _B =-2A/-0.2A *	
DC current	2SB1188,2SB1182 2SB1240,2SB891F		82		390		*	
transfer ratio	2SB822,2SB1277 2SB891F	hfe	120	_	390		Vc==-3V, lc=-0.5A	
Transition frequ	iency	fτ	_	100	_	MHz	Vc=-5V, l==0.5A, f=30MHz	
Output capacita	ance	Cob		50	_	pF	V _{CB} =-10V, I _E =0A, f=1MHz	

^{*} Measured using pulse current.

^{*2} On 40 x 40 x 0.7 mm ceramic board is used.

^{*3} Printed circuit board 1.7mm thick, collector copper plating 1cm² or larger.

●Packaging specifications and hre

		Package		Ta	Bulk			
		Code	T100	TL	TU2	TL2	_	
Туре	hre	Basic ordering unit (pieces)	1000	2500	2500	2500	1000	2000
2SB1188	PQF	1	0		_		_	_
2SB1182	PQF	}		0	_	_	_	<u>-</u>
2SB1240	QR			_	0	_	_	
2SB891F	PQF	7	-	_	_	_	0	_
2SB822	Q		T -	_	_	_	_	0
2SB1277	Q		-		-	0		
2SB911M	Q		_	_	_	_		0

hre values are classified as follows:

ltem	Р	Q	R	
hre	82~180	120~270	180~390	

Electrical characteristic curves

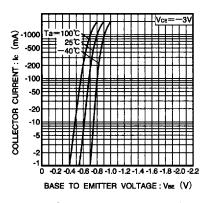


Fig.1 Grounded emitter propagation characteristics

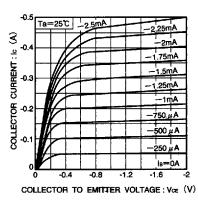


Fig.2 Grounded emitter output characteristics

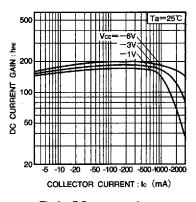
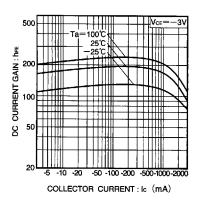
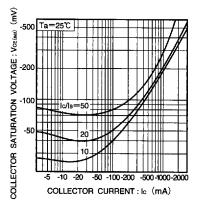


Fig.3 DC current gain vs. collector current (I)

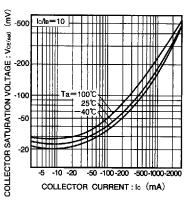
7828999 0016863 103 | **ROHM**



DC current gain vs. collector current (I)



Collector-emitter saturation voltage vs. collector current (I)



Collector-emitter saturation voltage vs. collector current (II)

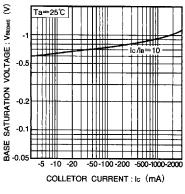


Fig.7 Base-emitter saturation voltage vs. collector current

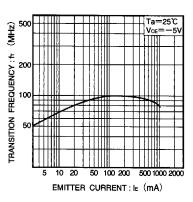
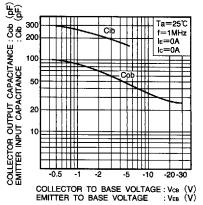


Fig.8 Gain bandwidth product vs. emitter current



Collector output capacitance vs. collector-base voltage Emitter input capacitance vs. emitter-base voltage

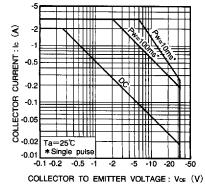


Fig.10 Safe operation area (2SB1188)

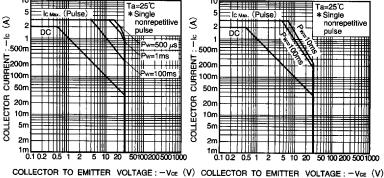


Fig.11 Safe operation area

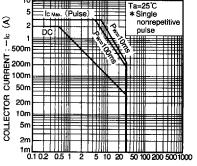


Fig.12 Safe operation area (2SB891)

(2SB1182)

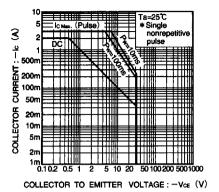
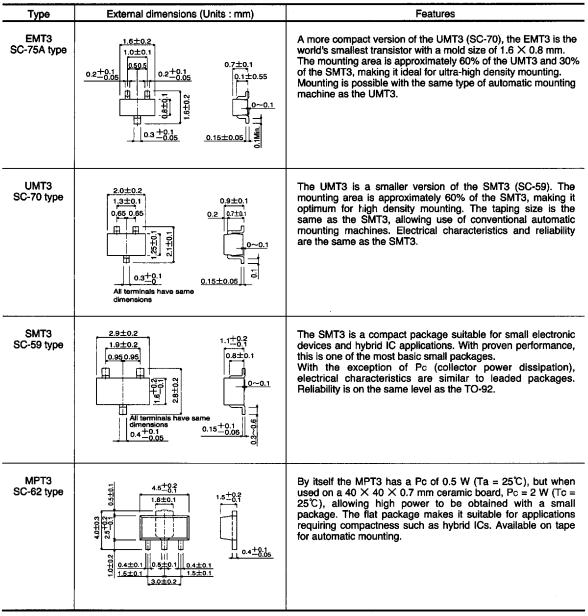


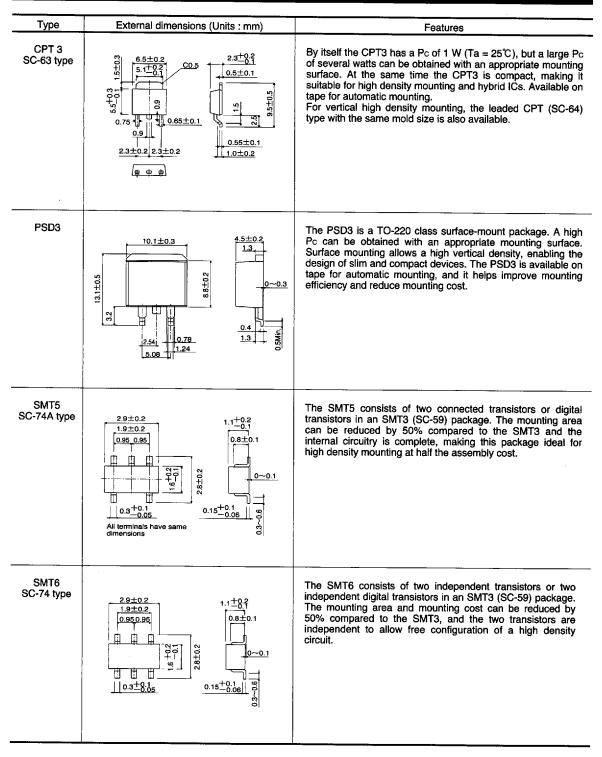
Fig.13 Safe operation area (2SB891 (TO-126M))

Packages

ROHM has been manufacturing transistors since 1975. In the development of products, we constantly strive to anticipate the needs of our customers. Regarding packages, the demands of the market for compactness, low power consumption, low power dissipation and automatic mounting support are becoming ever greater, and we are strengthening our product development system to meet these needs.

Types and features of surface-mount packages

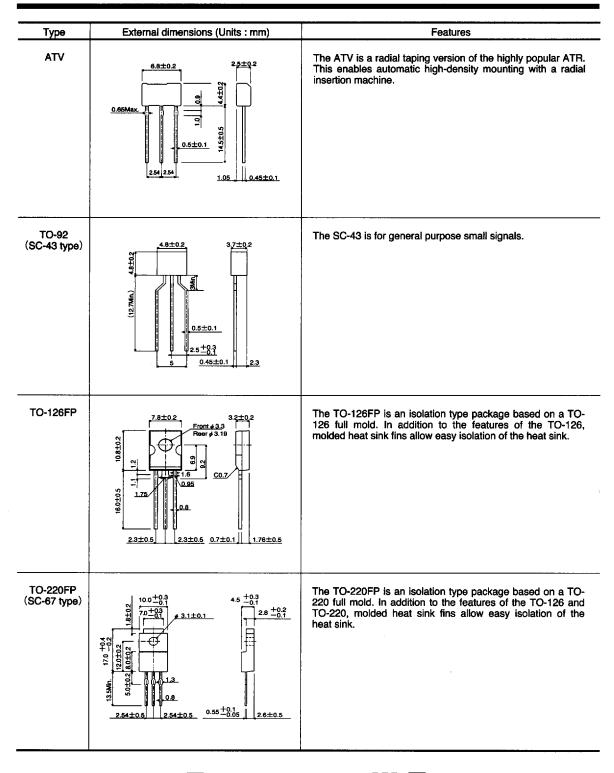




Туре	External dimensions (Units : mm)	Features
UMT5 SC-88A type	2.0±0.2 1,3±0.1 0,65 0.65 0.7 0.7 0.005 All terminals have same dimensions	The UMT5 consists of two connected transistors or digital transistors in a UMT3 (SC-70) package. The mounting area can be reduced by 50% compared to the UMT3 and the internal circuitry is completed, making this package ideal for high density mounting at half the assembly cost.
UMT6 SC-88 type	2.0±0.2 1.3±0.1 0.65 0.65 0.7 0.7 0.7 0.7 0.7 0.7 0.7 0.7	The UMT6 consists of two independent transistors or two independent digital transistors in a UMT (SC-70) package. The mounting area and mounting cost can be reduced by 50% compared to the UMT3, and the two transistors are independent to allow free configuration of a high density circuit.

▲ Typee	and	festures	Ωf	haheal	packages
TIVUES	anu	reatures	OI	leaded	Dackages

Туре	External dimensions (Units : mm)	Features
SPT (SC-72 type)	2±0,2 0.45±0.15 0.45±0.15 0.5 0.45±0.15 0.5 0.45±0.15	The SPT is a smaller version of the conventional TO-92 type. The body size (3×4×2 mm³) has been reduced to 1/4 that of the TO-92 (5×5×4 mm³). The SPT is available on tape for automatic insertion, and less space is occupied on the printed circuit board than the TO-92. Reliability is the same as the TO-92.
FTR	0.65±0.1 2.4±0.2 0.55±0.1 0.45±0.1 0.45±0.1	SIL type with a height of 3.4 mm and a lead pitch of 2.54 mm.
FTL	0.65Max 2.4±0.2 0.5±0.1 0.5±0.1	The FTL is a radial taping version of the highly popular FTR. This enables automatic high-density mounting with a radial insertion machine.
ATR (SC-71 type)	0.65Max 0.65Max 0.65 0.4 0.55±0.1 0.55±0.1 0.45±0.1	SC-71type with a height of 4.4 mm and a Pc=1W type.



Туре	External dimensions (Units : mm)	Features
TO-220FN	\$3.2±0.2 \$3.2±0	The TO-220FN features the same performance as the TO-220FP with approximately 2 mm less height, allowing the design of slimmer devices. Furthermore, the elimination of support pins in the fin (collector electrode) solves short-circuiting problems with neighboring components and the chassis. To make the height to the installation hole the same as the TO-220FP, it can be replaced as is from the TO-220FP.